ATTACHMENT A

Shaping silicon tiles in Step 702 includes shaping silicon tiles from a material selected from the group including single-crystal silicon (c-Si) and polycrystalline silicon (p-Si). In some aspects the silicon tiles are shaped from a silicon material doped with a p-type dopant with a resistivity in the range from 0.5 to 50 ohms per centimeter.

Step 704 treats the silicon tile edges to minimize the generation of contaminating particles. Step 704 treats the silicon tiles by subjecting the silicon tile top and bottom surface edges to a treatment selected from the group including beveling and radiusing. In Step 704a the silicon tile top surface edges are beveled within the range of 1 mm to 5 mm. Alternately, the silicon tile top surface edges are radiused within the range of 3 mm to 10 mm. In Step 704b the silicon tile bottom edges are beveled approximately 1.5 mm.

Step 704c includes subjecting the silicon tile corners to a treatment selected from the group including beveling and radiusing. In one aspect the silicon tile corners are beveled approximately 1.5 mm.

Step 706, following the treating of the silicon tile edges in Step 704, chemically etches the silicon tile surfaces. Chemically etching the silicon tile surfaces includes removing silicon material within the range of 50 microns (um) to 500 um. In some aspects chemically etching the silicon tile surfaces includes immersing the silicon tiles in a solution selected from the group including HNO3/HF/CH3COOH (4:1:3) and HF/HNO3 (1.6:1.8). Alternately, the chemically etching of the silicon tile surfaces in Step 706 includes